Diode Module

Features

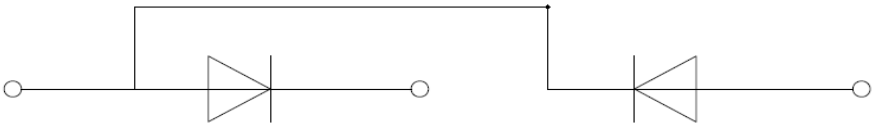
- A package of series of two diodes
- Heat transfer through alumina ceramic and metal substrate
- Welding by vacuum welding technology, which provide high reliability

Product Summary

Parameter	Value	Unit
V_{RRM}	2000	V
$I_{F(AV)}$(@ T_C = 100)	136	A
I_{FSM}(@ t_P = 10ms)	3640	A
V_F(Max)	1.60	V

Applications

- AC converter
- Inverter
- DC motor



Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	2000	V
Non-repetitive peak reverse voltage	T_{vj} = 25°C	V_{RSM}	2100	V
Average forward current	T_C = 100°C	$I_{F(AV)}$	136	A
Forward surge current	1/2 cycle, Sine wave, 50Hz T_{vj} = 25	I_{FSM}	3640	A
I^2t value for fusing		I^2t	66200	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

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Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	I_F=410A, t_P=380	V_F			1.60	V
Reverse leakage current	$V_R = V_{RRM}, T_{vj}$ = 25	I_{RRM}			100	A
	$V_R = V_{RRM}, T_{vj}$ = 150				50	mA
Threshold voltage	T_{vj} = 150 , for power loss calculation only	V_{TO}			0.85	V
Dynamic resistance		r_T			1.5	m

Thermal Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	

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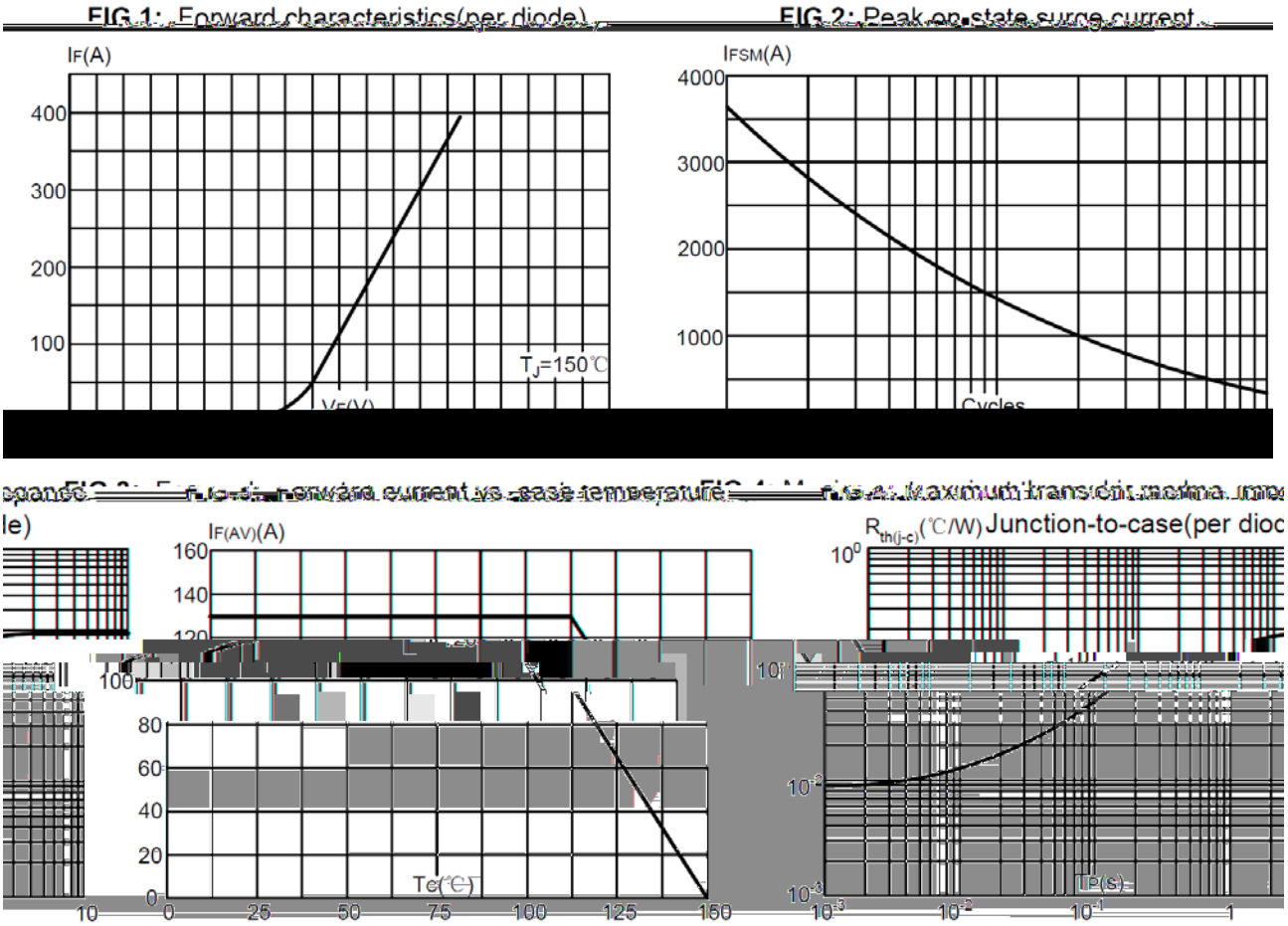
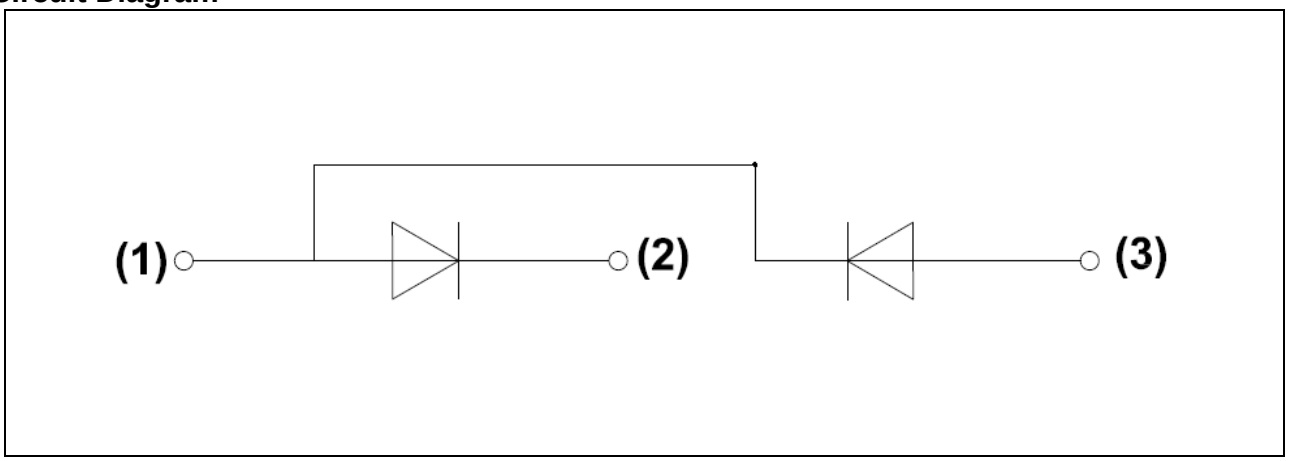
Typical Electrical & Thermal Characteristics



Circuit Diagram



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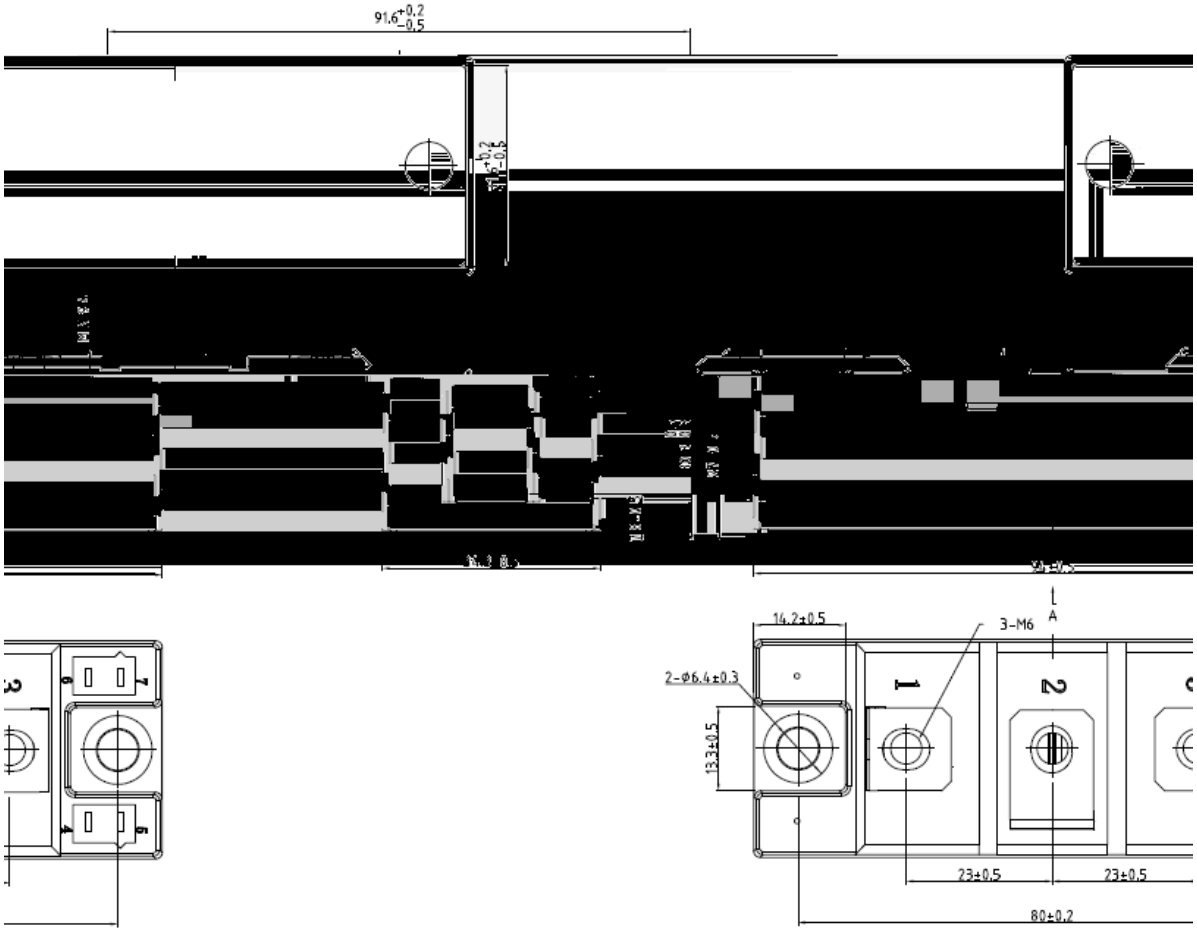
Package Outlines (mm)



Unit of measurement: mm

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